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12 comparison logic for comparing the digital values with limit values, generating flag
13 values based on the limit values, and storing the flag values in predefined locations within the
memory.

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1 2. The single-chip integrated circuit of claim 1, further including:
2 a cumulative clock for generating a time value corresponding to cumulative operation
3 time of the transceiver, wherein the generated time value is readable via the interface.

1 3. The single-chip integrated circuit of claim 1, further including:
2 a cumulative clock for generating and storing in a register a time value corresponding
3 to cumulative operation time of the transceiver, wherein the register in which the time value
4 is stored comprises one of the memory arrays of the memory.

5 4. The single-chip integrated circuit of claim 1, further including:
6 a power supply voltage sensor coupled to the analog to digital conversion circuitry,
7 the power supply voltage sensor generating a power level signal corresponding to a power
8 supply voltage level of the transceiver, wherein the analog to digital conversion circuitry is
9 configured to convert the power level signal into a digital power level value and to store the
10 digital power level value in a predefined power level location within the memory.

1 5. The single-chip integrated circuit of claim 4, further including:
2 a temperature sensor coupled to the analog to digital conversion circuitry, the
3 temperature sensor generating a temperature signal corresponding to a temperature of the
4 transceiver, wherein the analog to digital conversion circuitry is configured to convert the
5 temperature signal into a digital temperature value and to store the digital temperature value
6 in a predefined temperature location within the memory.

1 6. The single-chip integrated circuit of claim 5, wherein
2 the comparison logic includes logic for comparing the digital power level value with a
3 power level limit value, generating a power level flag value based on the comparison of the

4 digital power level signal with the power level limit value, and storing the power level flag
5 value in a predefined power level flag location within the memory; and

6 the comparison logic includes logic for comparing the digital temperature value with a
7 temperature limit value, generating a temperature flag value based on the comparison of the
8 digital temperature signal with the temperature limit value, and storing the temperature flag
9 value in a predefined temperature flag location within the memory.

1 7. The single-chip integrated circuit of claim 4, wherein
2 the comparison logic includes logic for comparing the digital power level value with a
3 power level limit value, generating a power level flag value based on the comparison of the
4 digital power level signal with the power level limit value, and storing the power level flag
5 value in a predefined power level flag location within the memory.

1 8. The single-chip integrated circuit of claim 1, further including:
2 a temperature sensor coupled to the analog to digital conversion circuitry, the
3 temperature sensor generating a temperature signal corresponding to a temperature of the
4 transceiver, wherein the analog to digital conversion circuitry is configured to convert the
5 temperature signal into a digital temperature value and to store the digital temperature value
in a predefined temperature location within the memory.
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further*

1 9. The single-chip integrated circuit of claim 8, wherein
2 the comparison logic includes logic for comparing the digital temperature value with a
3 temperature limit value, generating a temperature flag value based on the comparison of the
4 digital temperature signal with the temperature limit value, and storing the temperature flag
5 value in a predefined temperature flag location within the memory.

1 10. The single-chip integrated circuit of claim 1, further including
2 fault handling logic, coupled to the transceiver for receiving at least one fault signal
3 from the transceiver, coupled to the memory to receive at least one flag value stored in the
4 memory, and coupled to a host interface to transmit a computed fault signal, the fault
5 handling logic including computational logic for logically combining the at least one fault

6 signal received from the transceiver and the at least one flag value received from the memory
7 to generate the computed fault signal.

1 11. The single-chip integrated circuit of claim 1, further including
2 control adjustment circuitry for adjusting a first control signal of the control signals
3 generated by the control circuitry in accordance with an adjustment value stored in the
4 memory.

1 12. The single-chip integrated circuit of claim 1, wherein the control circuitry generates
2 the first control signal in accordance with a temperature.

1 13. The single-chip integrated circuit of claim 1, wherein the plurality of analog signals
2 includes two analog signals selected from the set consisting of laser bias current, laser output
3 power, and received power.

1 14. (amended) A single-chip integrated circuit for monitoring an optoelectronic device,
2 comprising:

3 memory, including one or more memory arrays for storing information related to the
4 optoelectronic device;

5 analog to digital conversion circuitry for receiving a plurality of analog signals from
6 the optoelectronic device, the analog signals corresponding to operating conditions of the
7 optoelectronic device, converting the received analog signals into digital values, and storing
8 the digital values in predefined locations within the memory; and

9 a memory interface for reading from and writing to locations within the memory in
10 accordance with commands received from a host device.

1 15. The single-chip integrated circuit of claim 14, further including:

2 a cumulative clock for generating a time value corresponding to cumulative operation
3 time of the optoelectronic device, wherein the generated time value is readable via the
4 memory interface.

1 16. The single-chip integrated circuit of claim 14, further including:
2 a cumulative clock for generating and storing in a register a time value corresponding
3 to cumulative operation time of the optoelectronic device, wherein the register in which the
4 time value is stored comprises one of the memory arrays of the memory.

1 17. The single-chip integrated circuit of claim 14, further including:
2 a power supply voltage sensor coupled to the analog to digital conversion circuitry,
3 the power supply voltage sensor generating a power level signal corresponding to a power
4 supply voltage level of the optoelectronic device, wherein the analog to digital conversion
5 circuitry is configured to convert the power level signal into a digital power level value and to
6 store the digital power level value in a predefined power level location within the memory.

1 18. The single-chip integrated circuit of claim 17, further including:
2 comparison logic for comparing the digital power level value with a power level limit
3 value, generating a power level flag value based on the comparison of the digital power level
4 signal with the power level limit value, and storing the power level flag value in a predefined
5 power level flag location within the memory.

1 19. The single-chip integrated circuit of claim 18, further including
2 a temperature sensor coupled to the analog to digital conversion circuitry, the
3 temperature sensor generating a temperature signal corresponding to a temperature of the
4 optoelectronic device, wherein the analog to digital conversion circuitry is configured to
5 convert the temperature signal into a digital temperature value and to store the digital
6 temperature value in a predefined temperature location within the memory.

1 20. The single-chip integrated circuit of claim 19, wherein
2 the comparison logic includes logic for comparing the digital temperature value with a
3 temperature limit value, generating a temperature flag value based on the comparison of the
4 digital temperature signal with the temperature limit value, and storing the temperature flag
5 value in a predefined temperature flag location within the memory.

1 21. The single-chip integrated circuit of claim 14, further including
2 a temperature sensor coupled to the analog to digital conversion circuitry, the
3 temperature sensor generating a temperature signal corresponding to a temperature of the
4 optoelectronic device, wherein the analog to digital conversion circuitry is configured to
5 convert the temperature signal into a digital temperature value and to store the digital
6 temperature value in a predefined temperature location within the memory.

1 22. The single-chip integrated circuit of claim 21, further including
2 comparison logic for comparing the digital temperature value with a temperature limit
3 value, generating a temperature flag value based on the comparison of the digital temperature
4 signal with the temperature limit value, and storing the temperature flag value in a predefined
5 temperature flag location within the memory.

1 23. The single-chip integrated circuit of claim 14, further including
2 fault handling logic, coupled to the optoelectronic device for receiving at least one
3 fault signal from the optoelectronic device, coupled to the memory to receive at least one flag
4 value stored in the memory, and coupled to a host interface to transmit a computed fault
5 signal, the fault handling logic including computational logic for logically combining the at
6 least one fault signal received from the optoelectronic device and the at least one flag value
7 received from the memory to generate the computed fault signal.

1 24. The single-chip integrated circuit of claim 14, wherein the plurality of analog signals
2 includes two analog signals selected from the set consisting of laser bias current, laser output
3 power, and received power.

1 25. A single-chip integrated circuit for controlling an optoelectronic transceiver having a
2 laser transmitter and a photodiode receiver, comprising:
3 analog to digital conversion circuitry for receiving a plurality of analog signals from
4 the laser transmitter and photodiode receiver, converting the received analog signals into

5 digital values, and storing the digital values in predefined memory mapped locations within
6 the integrated circuit;

7 comparison logic for comparing the digital values with limit values, generating flag
8 values based on the limit values, and storing the flag values in predefined memory mapped
9 locations within the integrated circuit;

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B3> 10 control circuitry configured to generate control signals to control operation of the laser
11 transmitter in accordance with one or more values stored in the integrated circuit; and

12 a memory mapped interface for reading from and writing to locations within the
13 integrated circuit and for accessing memory mapped locations within the integrated circuit for
14 controlling operation of the control circuitry.

1 26. A method of controlling an optoelectronic transceiver having a laser transmitter and a
2 photodiode receiver, comprising:

3 in accordance with instructions received from a host device, reading from and writing
4 to locations within a memory; and

5 receiving a plurality of analog signals from the laser transmitter and photodiode
6 receiver, converting the received analog signals into digital values, and storing the digital
7 values in predefined locations within the memory;

8 comparing the digital values with limit values, generating flag values based on the
9 limit values, and storing the flag values in predefined locations within the memory;

10 generating control signals to control operation of the laser transmitter in accordance
11 with one or more values stored in the memory.

1 27. The method of claim 26, further including:

2 generating a time value corresponding to cumulative operation time of the transceiver,
3 wherein the generated time value is readable by the host device via the memory interface.

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B3> 1 28. The method of claim 26, further including:

2 generating and storing in a register a time value corresponding to cumulative
3 operation time of the transceiver, wherein the register in which the time value is accessed by
4 the reading step as a location in the memory.

1 29. The method of claim 26, further including:
2 converting an analog power supply voltage level signal, corresponding to a voltage
3 level of the transceiver, into a digital power level value and storing the digital power level
4 value in a predefined power level location within the memory.

1 30. The method of claim 29, further including:
2 generating a temperature signal corresponding to a temperature of the transceiver,
3 converting the temperature signal into a digital temperature value and storing the digital
4 temperature value in a predefined temperature location within the memory.

1 31. The method of claim 30, including
2 comparing the digital power level value with a power level limit value, generating a
3 power level flag value based on the comparison of the digital power level signal with the
4 power level limit value, and storing the power level flag value in a predefined power level
5 flag location within the memory; and

6 comparing the digital temperature value with a temperature limit value, generating a
7 temperature flag value based on the comparison of the digital temperature signal with the
8 temperature limit value, and storing the temperature flag value in a predefined temperature
9 flag location within the memory.

1 32. The method integrated circuit of claim 29, including
2 comparing the digital power level value with a power level limit value, generating a
3 power level flag value based on the comparison of the digital power level signal with the
4 power level limit value, and storing the power level flag value in a predefined power level
5 flag location within the memory.

1 33. The method of claim 26, further including:

2 generating a temperature signal corresponding to a temperature of the transceiver,
3 converting the temperature signal into a digital temperature value and storing the digital
4 temperature value in a predefined temperature location within the memory.

1 34. The method of claim 33, including:

2 comparing the digital temperature value with a temperature limit value, generating a
3 temperature flag value based on the comparison of the digital temperature signal with the
4 temperature limit value, and storing the temperature flag value in a predefined temperature
5 flag location within the memory.

1 35. The method of 26, further including

2 receiving at least one fault signal from the transceiver, receiving at least one flag value
3 stored in the memory, logically combining the at least one fault signal received from the
4 transceiver and the at least one flag value received from the memory to generate a computed
5 fault signal, and transmitting the computed fault signal to the host device.

1 36. The method of claim 26, further including

2 adjusting a first control signal of the control signals in accordance with an adjustment
3 value stored in the memory.

1 37. The method of claim 26, wherein the method is performed by a single-chip controller
2 integrated circuit.

1 38. The method of claim 26, wherein the plurality of analog signals includes two analog
2 signals selected from the set consisting of laser bias current, laser output power, and received
3 power.

1 39. (amended) A method of monitoring an optoelectronic device, comprising:

2 in accordance with instructions received from a host device, reading from and writing
3 to locations within a memory; and

5 receiving a plurality of analog signals from the optoelectronic device, the analog
6 signals corresponding to operating conditions of the optoelectronic device, converting the
7 received analog signals into digital values, and storing the digital values in predefined
8 locations within the memory;

9 wherein the method is performed by a single-chip controller integrated circuit.

1 40. The method of claim 39, further including:

2 generating a time value corresponding to cumulative operation time of the transceiver,
3 wherein the generated time value is readable by the host device via the memory interface.

1 41. The method of claim 39, further including:

2 generating and storing in a register a time value corresponding to cumulative
3 operation time of the transceiver, wherein the register in which the time value is accessed by
4 the reading step as a location in the memory.

1 42. The method of claim 39, further including:

2 generating a power level signal corresponding to a power supply voltage level of the
3 optoelectronic device, converting the power level signal into a digital power level value and
4 storing the digital power level value in a predefined power level location within the memory.

1 43. The method of claim 39, further including:

2 comparing the digital power level value with a power level limit value, generating a
3 power level flag value based on the comparison of the digital power level signal with the
4 power level limit value, and storing the power level flag value in a predefined power level
5 flag location within the memory.

1 44. The method of claim 43, further including

2 generating a temperature signal corresponding to a temperature of the optoelectronic
3 device, converting the temperature signal into a digital temperature value and storing the
4 digital temperature value in a predefined temperature location within the memory.

1 45. The method of claim 44, wherein
2 comparing the digital temperature value with a temperature limit value, generating a
3 temperature flag value based on the comparison of the digital temperature signal with the
4 temperature limit value, and storing the temperature flag value in a predefined temperature
5 flag location within the memory.

1 46. The method of claim 39, further including
2 generating a temperature signal corresponding to a temperature of the optoelectronic
3 device, wherein the analog to digital conversion circuitry is configured to convert the
4 temperature signal into a digital temperature value and to store the digital temperature value
5 in a predefined temperature location within the memory.

1 47. The method of claim 46, further including
2 comparing the digital temperature value with a temperature limit value, generating a
3 temperature flag value based on the comparison of the digital temperature signal with the
4 temperature limit value, and storing the temperature flag value in a predefined temperature
5 flag location within the memory.

1 48. The method of claim 39, further including
2 receiving at least one fault signal from the optoelectronic device, receiving at least one
3 flag value stored in the memory, logically combining the at least one fault signal received
4 from the optoelectronic device and the at least one flag value received from the memory to
5 generate a computed fault signal, and transmit the computed fault signal to the host device.

1 49. The method of claim 39, wherein the plurality of analog signals includes two analog
2 signals selected from the set consisting of laser bias current, laser output power, and received
3 power.

1 50. A method of controlling an optoelectronic transceiver having a laser transmitter and a
2 photodiode receiver, comprising:

3 in accordance with instructions received from a host device, reading from and writing
4 to memory mapped locations within a controller of the optoelectronic transceiver;
5 receiving a plurality of analog signals from the laser transmitter and photodiode
6 receiver, converting the received analog signals into digital values, and storing the digital
7 values in predefined memory mapped locations within the controller;
8 comparing the digital values with limit values, generating flag values based on the
9 limit values, and storing the flag values in predefined memory mapped locations within the
10 controller;
11 generating control signals to control operation of the laser transmitter in accordance
12 with one or more values stored in the predefined memory mapped locations within the
13 controller;
14 analog to digital conversion circuitry for receiving a plurality of analog signals from
15 the laser transmitter and photodiode receiver, converting the received analog signals into
16 digital values, and storing the digital values in predefined memory mapped locations within
17 the controller.

1 51. The method of claim 50, further including:
2 generating and storing in a register a time value corresponding to cumulative
3 operation time of the transceiver, wherein the register in which the time value is accessed by
4 the reading step as a memory mapped within the controller.

New claims:

1 52. (new) A single-chip integrated circuit for monitoring an optoelectronic device,
2 comprising:
3 memory, including one or more memory arrays for storing information related to the
4 optoelectronic device;
5 analog to digital conversion circuitry configured to receive a plurality of analog
6 signals, the analog signals corresponding to operating conditions of the optoelectronic device,
7 converting at least one of the received analog signals into at least one digital value, and

8 storing the at least one digital value in at least one predefined location within the memory;

9 and

10 a memory interface for reading from and writing to locations within the memory in
11 accordance with commands received from a host device.

12 53. (new) The single-chip integrated circuit of claim 52, further including:

13 a temperature sensor coupled to the analog to digital conversion circuitry, the
14 temperature sensor generating a temperature signal corresponding to a temperature of the
15 transceiver, wherein the analog to digital conversion circuitry is configured to convert the
16 temperature signal into a digital temperature value and to store the digital temperature value
17 in the at least one predefined location within the memory.

1 54. (new) The single-chip integrated circuit of claim 52, wherein the analog to digital
2 conversion circuitry is configured to receive a voltage signal from a source external to the
3 single-chip integrated circuit, wherein the analog to digital conversion circuitry is configured
4 to convert the voltage signal into a digital voltage value and to store the digital voltage value
5 in the at least one predefined location within the memory.

1 55. (new) A single-chip integrated circuit for monitoring an optoelectronic device,
2 comprising:

3 memory, including one or more memory arrays for storing information related to the
4 optoelectronic device;

5 analog to digital conversion circuitry for receiving at least one analog signal, the at
6 least one analog signal corresponding to operating conditions of the optoelectronic device,
7 converting the at least one analog signal into at least one digital value, and storing the at least
8 one digital value in at least one predefined location within the memory; and

9 a memory interface for reading from and writing to locations within the memory in
10 accordance with commands received from a host device.

1 56. (new) The single-chip integrated circuit of claim 55, further including:

2 a temperature sensor coupled to the analog to digital conversion circuitry, the
3 temperature sensor generating a temperature signal corresponding to a temperature of the
4 transceiver, wherein the analog to digital conversion circuitry is configured to convert the
5 temperature signal into a digital temperature value and to store the digital temperature value
6 in the at least one predefined location within the memory.

1 57. (new) The single-chip integrated circuit of claim 55, further including control
2 circuitry, responsive to the digital temperature digital value for controlling operation of the
3 optoelectronic device.

1 58. (new) The single-chip integrated circuit of claim 55, wherein the analog to digital
2 conversion circuitry is configured to receive a voltage signal from a source external to the
3 single-chip integrated circuit, wherein the analog to digital conversion circuitry is configured
4 to convert the voltage signal into a digital voltage value and to store the digital voltage value
5 in the at least one predefined location within the memory.

1 59. (new) The single-chip integrated circuit of claim 55, further including control
2 circuitry, responsive to the at least one digital value for controlling operation of the
3 optoelectronic device.

1 60. (new) A method of monitoring an optoelectronic device, comprising:
2 storing, in one or more memory arrays, information related to the optoelectronic
3 device;
4 receiving at least one analog signal, the at least one analog signal corresponding to
5 operating conditions of the optoelectronic device;
6 converting the at least one analog signal into at least one digital value, and storing the
7 at least one digital value in at least one predefined location within the memory; and
8 reading from and writing to locations within the memory in accordance with
9 commands received from a host device.

1 61. (new) The method of claim 60, further including:

2 generating a temperature signal corresponding to a temperature of the transceiver;
3 the converting and storing steps including converting the temperature signal into a
4 digital temperature value, and storing the digital temperature value in the at least one
5 predefined location within the memory.

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2 62. (new) The method of claim 61, further including controlling operation of the
optoelectronic device in response to the digital temperature value.

1 *Concl*
2 63. (new) The method of claim 60, wherein
3 the receiving step includes receiving a voltage signal from a source external to the
single-chip integrated circuit,
4 the converting and storing steps include converting the voltage signal into a digital
5 voltage value and storing the digital voltage value in the at least one predefined location
6 within the memory.

1 64. (new) The method of claim 60, further including controlling operation of the
2 optoelectronic device in response to the at least one digital value.

Respectfully submitted,
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